Strain-induced large spin splitting and persistent spin helix at LaAlO$_3$/SrTiO$_3$ interface

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We investigated the effect of the tensile strain on the spin splitting at the n-type interface in LaAlO$_3$/SrTiO$_3$ in terms of the spin-orbit coupling coefficient $\alpha$ and spin texture using first-principles calculations. We found that the $\alpha$ could be controlled by the tensile strain and be enhanced up to 5 times for the tensile strain of 7%, and the effect of the tensile strain leads to a persistent spin helix, which has a long spin lifetime. These results support that the strain effect on LaAlO$_3$/SrTiO$_3$ is important for various applications such as spinFET and spin-to-charge conversion.

The LaAlO$_3$/SrTiO$_3$ interface is one of the most important heterostructures, which has an n-type interface with high mobility two-dimensional electronic gas (2DEG).$^{1,2}$ Recently, Rashba effect in LaAlO$_3$/SrTiO$_3$ has attracted much attention due to potential applications in spintronics.$^3$ For example, spin-to-charge conversion phenomenon induced by the inverse Rashba–Edelstein effect (IREE) for LaAlO$_3$/SrTiO$_3$ was reported.$^4$ IREE can be used for an alternative mechanism of detection of spin current utilizing inverse spin Hall effect,$^5$ and it is suggested that the strength of the IREE was proportional to the Rashba coefficient $\alpha_R$. Therefore, it is quite important to control the Rashba effect at the LaAlO$_3$/SrTiO$_3$ interface.

The applied electric field can control the magnitude of $\alpha_R$. The $\alpha_R$ in LaAlO$_3$/SrTiO$_3$ induced by built-in electric field was experimentally evaluated as 18 meV Å, and it was increased up to 49 meVÅ by applying electric field.$^3$ In epitaxial oxide thin films and superlattices, strain induced by substrates, is useful to control electronic structures and physical properties, and so important that its effects are extensively studied for various materials.$^7$ Some works about the strain for LaAlO$_3$/SrTiO$_3$ actually were reported.$^8,9$ Bulk SrTiO$_3$ shows strain-induced ferroelectric phase transition,$^{10}$ and the electric polarization is induced by the tensile strain along the [110]-direction. Since the 2DEG at the n-type interface in LaAlO$_3$/SrTiO$_3$ may be influenced by the strain-induced electric polarization, the spin splitting, especially spin-orbit coupling coefficient $\alpha$, can be controlled by the strain. In fact, a first-principles calculation of strain control of the Rashba spin splitting in ZnO was reported.$^{11}$

In this work, we focus the spin splitting at the n-type interface in LaAlO$_3$/SrTiO$_3$, and investigate the effect of tensile strain on it in terms of the spin-orbit coupling coefficient $\alpha$ and spin texture using first-principles calculations. We found that the $\alpha$ could be controlled by the tensile strain and be enhanced up to 5 times for the tensile strain of 7%, and the effect of the tensile strain leads to a persistent spin helix, which has a long spin lifetime. These properties are expected to be important to various spintronic applications. Rashba effect arises from spin-orbit interaction for the 2DEG at the surfaces and interfaces with the spatial inversion symmetry breaking, and the Hamiltonian describing Rashba effect in the 2DEG can be expressed by $H = -\hbar^2\nabla^2/(2m^*) + H_R$, where $\hbar$ is the Planck constant, and $m^*$ is the effective mass of electrons. The Rashba Hamiltonian: $H_R = \alpha_R(\hat{\epsilon} \times \hat{\kappa}) \cdot \vec{\sigma} = \alpha_R(k_x\sigma_y - k_y\sigma_x)$, where $\alpha_R$ denotes the Rashba coefficient, $\hat{\epsilon}$, the unit vector along $z$-axis, $\vec{\kappa}$ = (k$_x$, k$_y$, 0) the wave vector, and $\vec{\sigma}$ = (\sigma$_x$, \sigma$_y$, \sigma$_z$) the Pauli matrices vector, respectively. We can obtain the energy dispersion relation: $E_{\pm}(\vec{k}_f) = \hbar^2 k_f^2/(2m^*) \pm \alpha_R k_f$. The $\alpha_R$ satisfies $\alpha_R = 2E_R/k_R$, where $E_R$ = $\alpha_R^2/2(\hbar^2)$ is the Rashba energy, and $k_R$ = ($m^*/\alpha_R$)$^{1/2}$ the Rashba momentum offset.

For the interfacial system with the tensile strain in LaAlO$_3$/SrTiO$_3$, due to the strain-induced electric polarization along the [110]-direction originating from bulk SrTiO$_3$, there is expected to be only one mirror plane along the (110) plane. Indeed, we confirm that atomic displacement is induced along the (110) plane in atomic structures optimized by the first-principles calculation. Thus, the spin-orbit Hamiltonian can be expressed as $H_{z\perp} = \alpha_{\parallel}^1 k_x \sigma_y + \alpha_{\parallel}^1 k_y \sigma_x + \alpha_{[110]}^+(k_{\parallel} - k_{\perp})/2 \sigma_z$ in the same way as the analysis in the previous work of a ZnO (1010) surface with a mirror plane along the (100) plane.$^{13}$ While the $\alpha_{\parallel}^1$ and $\alpha_{\parallel}^2$, are corresponding to the Rashba effect, the $\alpha_{[110]}^+$ originates from the strain-induced electric polarization. As the tensile strain increases, $H_{z\perp}^\perp = \alpha_{[110]}^+ (k_{\parallel} - k_{\perp})/2 \sigma_z$ is expected to be more dominant. The spin texture for $H_{z\perp}^\perp$ has the spin splitting along the [110]-direction, and the $\alpha_{[110]}^+$ can be evaluated in the same way as $\alpha_R$ for the Rashba system: $\alpha_{[110]^\perp}^+ = 2E_R^\perp/k_{[110]^\perp}$. We take the $\alpha_R$ and $\alpha_{[110]^\perp}^+$ as $\alpha_{[110]}^+$ hereafter.

We perform density functional calculations using the computational model of the superlattice (LaAlO$_3$)$_n$(SrTiO$_3$)$_m$ shown in Fig. 1(a), where the n-type interface indicates the one between the TiO$_2$ and LaO layers. It was suggested that the number of the formula unit of LaAlO$_3$ or SrTiO$_3$ was required to be 6 to describe the metallic ground state with atomic relaxation.$^{14-17}$ We use the experimental lattice constants: $a_{LaAlO_3}^{AO}$=3.788 Å$^{18}$ for LaAlO$_3$; $a_{SrTiO_3}^{STO}$=3.905 Å$^{19}$ for SrTiO$_3$, and the supercell length $c$ is determined with the cell volume conserved. We assumed the biaxial misfit strain $(a - a_{STO}^{STO})/a$, where $a$ denotes the in-plane lattice constant (xy-plane), and the positive strain is tensile. Our calculations are performed within the general gradient approximation$^{20}$

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by OpenMX code,\textsuperscript{21} with the fully relativistic total angular momentum dependent pseudopotentials taking spin-orbit interaction (SOI) into account.\textsuperscript{22} We adopt norm-conserving pseudopotentials with an energy cutoff of 300 Ry for charge density including the 5s, 5p, 5d and 6s-states as valence states for La; 3s and 3p for Al; 2s and 2p for O; 4s, 4p and 5s for Sr; 3s, 3p, 3d and 4s for Ti. We use 8 × 8 × 1 regular k-point mesh. The numerical pseudo atomic orbitals are used as follows: the numbers of the s-, p-, d- and f-character orbitals are 3, 3, 1 and 1, respectively, for La; 3, 3, 1 and 0 for Al and O; 3, 2, 1 and 0 for Sr; 3, 3, 2 and 0 for Ti. The cutoff radii of La, Al, O, Sr and Ti are 6.0, 7.0, 5.0, 10.0 and 7.0, respectively, in units of Bohr.

The calculated band structure for the unstrained system is shown in Fig. 1(c), and Fig. 1(d) is the enlarged view of the interface bands around Γ-point.

We calculate the spin-orbit coupling coefficient $\alpha_{[1\bar{1}0]}$ along the [110]-direction (Γ → M') at the n-type interface for the spin splitting under the tensile strain inducing the 2DEG. With the tensile strain, we find larger spin splitting compared to the unstrained system as shown in Fig. 2(a). Figure 2(b) shows the strain dependence for the $\alpha_{[1\bar{1}0]}$ and the momentum offset $k_{[1\bar{1}0]}$ for the interfacial bands around Γ-point. Without strain, our calculated $\alpha_{[1\bar{1}0]}$ (7.49 meV·Å) is of the same order as the prior works (18 meV·Å (expt.));\textsuperscript{3} 12.6 meV·Å (theor.)).\textsuperscript{17} As the tensile strain increases, the magnitude of the $\alpha_{[1\bar{1}0]}$ increases. The strain-induced electric polarization from bulk SrTiO$_3$ may enhance the polarity along the [110]-direction (Γ → M), which makes $\alpha_{[1\bar{1}0]}$ larger. The $\alpha_{[1\bar{1}0]}$, that is, spin splitting can be controlled by the tensile strain to get the about 5 times larger $\alpha_{[1\bar{1}0]}$ for the tensile strain of 7%. The spin textures in the strained system may be effective for IREE since it shows the pairs of the opposite spin components in each Fermi arc: inner and outer ones (See Fig. 2(c), (d)), while it is not Rashba spin splitting. The magnitude of the $\alpha_{[1\bar{1}0]}$ as well as $\sigma_B$ can be considered to be directly connected to the efficiency of spin-to-charge conversion $\lambda_{\text{IREE}}$ due to the relation $\lambda_{\text{IREE}} = \sigma_B \tau_s / \hbar$,\textsuperscript{6} where $\tau_s$ is the spin relaxation time. The effect of the tensile strain may also enhance the $\lambda_{\text{IREE}}$ in LaAlO$_3$/SrTiO$_3$ up to 5 times so that the larger conversion may be realized than the previous work.\textsuperscript{31}

In order to obtain the information of the spin-orbit Hamiltonian inducing the spin splitting, we calculate spin textures shown in Fig. 3. For the unstrained case (0%), our calculated spin texture shown in Fig. 3(a) shows a typical Rashba spin splitting, which is an agreement with the previous study.\textsuperscript{17} As the tensile strain increases, however, the nature of the spin texture changes dramatically. For the tensile strain (See Fig. 3(b), (c)), the spin texture is different from the Rashba-type one, and also has the nonzero out-of-plane component that can be considered to originate from the spin-orbit Hamiltonian $H_{\text{[1\bar{1}0]}} = \alpha_{[1\bar{1}0]} \frac{\hbar}{\sqrt{2}} \bigg( \frac{k_x}{\sqrt{2}} \bigg) \sigma_z$. In this case, the out-of-plane ($\sigma_z$) component is almost constant for the k-points except part of the Fermi arc around the degenerate points in the [110]-direction ($\theta = 45^\circ, -135^\circ$) so that the electronic states may have a long spin lifetime. This suggests that the persistent spin helix (PSH)\textsuperscript{13,24,25} may be formed. PSH has one-dimensionally-oriented spin components and is important for spin field-effect transistor (spinFET)\textsuperscript{26} due to its long.

\begin{figure*}[h]
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\caption{(a) Computational model. (b) Schematic of the first Brillouin zone. (c) Band structure for unstrained LaAlO$_3$/SrTiO$_3$. The red curves show the bands with the Rashba spin splitting. (d) Enlarged view for the interface bands around Γ-point.}
\end{figure*}

\begin{figure*}[h]
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\includegraphics[width=\textwidth]{figure2.png}
\caption{(a) Enlarged view for the interfacial bands about the spin splitting at the tensile strain of 5%. (b) Strain dependence for the spin-orbit coefficient $\alpha_{[1\bar{1}0]}$ and the momentum offset $k_{[1\bar{1}0]}$. (c) Spin textures at the tensile strain of 5%. (d) Fermi arcs at the tensile strain of 5%.}
\end{figure*}
spatial lifetime.\textsuperscript{24} As shown in Fig. 2(c), the spin components are one-dimensionally oriented at the tensile strain of 5%. The estimated PSH period $\lambda_{PSH}$ is $\pi/k_{[110]} = 0.098 \, \mu$m, which is comparable with that for a ZnO (10\,10) surface (0.19 $\mu$m),\textsuperscript{13} and is two order of magnitude smaller than that for a GaAs/AIGaAs quantum well (7.3-10 $\mu$m).\textsuperscript{27} Therefore, the PSH state of strained LaAlO$_3$/SrTiO$_3$ is suitable for miniaturization of spintronic devices.

In summary, we have performed first-principles density functional calculations for the n-type interface in LaAlO$_3$/SrTiO$_3$ with the tensile strain. We found that the spin-orbit coupling coefficient $\alpha$ directly connected to IREE could be controlled by the tensile strain and enhanced up to 5 times for the tensile strain of 7%. The PSH may be induced for the tensile strain so that the extremely long spin lifetime can be achieved. Moreover, the estimated PSH period $\lambda_{PSH}$ is comparable with that for a ZnO (10\,10) surface and is also two order of magnitude smaller than that for a GaAs/AIGaAs quantum well.\textsuperscript{27} The 2DEG in oxide surfaces is comparable with that for a ZnO (10\,10) surface and is two order of magnitude smaller than that for a GaAs (10\,-10) surface.\textsuperscript{27} Two sets of spin textures utilizing PSH. These results support that the strain effect in LaAlO$_3$/SrTiO$_3$ is important for various applications such as spinFET and spin-to-charge conversion.

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15) M. Park, S. Rhim and A. Freeman: Physical Review B.